

Jun Chen

List of Publications by Year in descending order

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65
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docs citations

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times ranked

912
citing authors

#	ARTICLE	IF	CITATIONS
1	Atomic-scale investigation of implanted Mg in GaN through ultra-high-pressure annealing. Journal of Applied Physics, 2022, 131, .	1.1	8
2	Electron-Beam-Induced Current and Cathodoluminescence Study of Dislocations in SrTiO ₃ . Crystals, 2020, 10, 736.	1.0	3
3	Influence of implanted Mg concentration on defects and Mg distribution in GaN. Journal of Applied Physics, 2020, 128, .	1.1	16
4	Photoelectron spectroscopic study on electronic state of corundum In ₂ O ₃ epitaxial thin film grown by mist-CVD. Japanese Journal of Applied Physics, 2020, 59, SIIG12.	0.8	4
5	Mg diffusion and activation along threading dislocations in GaN. Applied Physics Letters, 2020, 116, .	1.5	12
6	Electron-Beam-Induced Current Study of Dislocations and Leakage Sites in GaN Schottky Barrier Diodes. Journal of Electronic Materials, 2020, 49, 5196-5204.	1.0	3
7	Cathodoluminescence and scanning transmission electron microscopy study of InGaN/GaN quantum wells in core-shell GaN nanowires. Applied Physics Express, 2019, 12, 085003.	1.1	12
8	Anisotropic mosaicity and lattice-plane twisting of an <i>m</i> -plane GaN homoepitaxial layer. CrystEngComm, 2019, 21, 4036-4041.	1.3	5
9	Oxygen vacancy migration along dislocations in SrTiO ₃ studied by cathodoluminescence. Journal Physics D: Applied Physics, 2019, 52, 475103.	1.3	12
10	Wafer-scale analysis of GaN substrate wafer by imaging cathodoluminescence. Applied Physics Express, 2019, 12, 051005.	1.1	5
11	Cathodoluminescence study of Mg implanted GaN: the impact of dislocation on Mg diffusion. Applied Physics Express, 2019, 12, 051010.	1.1	25
12	Investigation of Si Dendrites by Electron-Beam-Induced Current. Crystals, 2018, 8, 317.	1.0	1
13	Investigation of dislocations in Nb-doped (100) SrTiO ₃ single crystals and their impacts on resistive switching. Superlattices and Microstructures, 2016, 99, 182-185.	1.4	5
14	Effect of Σ 3 generation on random grain boundaries in multicrystalline silicon. Superlattices and Microstructures, 2016, 99, 136-139.	1.4	3
15	Grassy Silica Nanoribbons and Strong Blue Luminescence. Scientific Reports, 2016, 6, 34231.	1.6	6
16	Defect Characterization in Silicon by Electron-Beam-Induced Current and Cathodoluminescence Techniques. Lecture Notes in Physics, 2015, , 343-373.	0.3	3
17	Control of extended defects in cast multicrystalline silicon using polycrystalline template. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1099-1102.	0.8	1
18	Control of extended defects in cast and seed cast Si ingots for photovoltaic application. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1094-1098.	0.8	0

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19	Grain boundary interactions in multicrystalline silicon grown from small randomly oriented seeds. Applied Physics Express, 2015, 8, 035502.	1.1	24
20	Investigation of dislocations in Nb-doped SrTiO ₃ by electron-beam-induced current and transmission electron microscopy. Applied Physics Letters, 2015, 106, 102109.	1.5	10
21	In situ monitoring of stacking fault formation and its carrier lifetime mediation in p-type 4H-SiC. Applied Physics Letters, 2014, 105, 042104.	1.5	9
22	Grain growth of cast-multicrystalline silicon grown from small randomly oriented seed crystal. Journal of Crystal Growth, 2014, 401, 717-719.	0.7	30
23	Local electrical properties of n-AlInAs/i-GaNAs electron channel structures characterized by the probe-electron-beam-induced current technique. Microscopy (Oxford, England), 2014, 63, 161-166.	0.7	3
24	Butterfly-shaped distribution of SiN precipitates in multi-crystalline Si for solar cells. Journal of Crystal Growth, 2013, 377, 37-42.	0.7	14
25	10 cm Diameter Mono Cast Si Growth and its Characterization. Solid State Phenomena, 2013, 205-206, 89-93.	0.3	4
26	Analysis of Inhomogeneous Dislocation Distribution in Multicrystalline Si. Solid State Phenomena, 2013, 205-206, 77-82.	0.3	0
27	Segregation Behaviors and Radial Distribution of Dopant Atoms in Silicon Nanowires. Nano Letters, 2011, 11, 651-656.	4.5	72
28	Image instability during the electrical measurement in scanning electron microscope. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1407-1411.	0.8	0
29	Electrical and optical activities of small angle grain boundaries in multicrystalline Si. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1347-1350.	0.8	4
30	Effect of Introducing $\hat{1}^2$ -FeSi ₂ Template Layers on Defect Density and Minority Carrier Diffusion Length in Si Region near p- $\hat{1}^2$ -FeSi ₂ /n-Si Heterointerface. Japanese Journal of Applied Physics, 2011, 50, 041303.	0.8	0
31	Minority-carrier diffusion length, minority-carrier lifetime, and photoresponsivity of $\hat{1}^2$ -FeSi ₂ layers grown by molecular-beam epitaxy. Journal of Applied Physics, 2011, 109, 123502.	1.1	11
32	Quantitative Photoelastic Characterization of Residual Strains in Grains of Multicrystalline Silicon. Journal of Electronic Materials, 2010, 39, 700-703.	1.0	16
33	Electrical and Optical Properties of Stacking Faults in 4H-SiC Devices. Journal of Electronic Materials, 2010, 39, 684-687.	1.0	14
34	Pre-existing and process induced defects in high-k gate dielectrics ∼ direct observation with EBIC and impact on 1/f noise ∼. , 2010, , .		1
35	(Invited) An Electron-Beam-Induced Current Investigation of Electrical Defects in High-k Gate Stacks. ECS Transactions, 2010, 28, 299-313.	0.3	7
36	Trap-Related Carrier Transports in p-Channel Field-Effect Transistor with Polycrystalline Si/HSiON Gate Stack. Japanese Journal of Applied Physics, 2009, 48, 04C005.	0.8	0

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37	Electron-Beam-Induced Current Study of Breakdown Behavior of High-K Gate MOSFETs. Solid State Phenomena, 2009, 156-158, 461-466.	0.3	1
38	Electrical activities of stacking faults and partial dislocations in 4H-SiC homoepitaxial films. Superlattices and Microstructures, 2009, 45, 295-300.	1.4	8
39	Structural characterization and iron detection at $\sim 3^\circ$ grain boundaries in multicrystalline silicon. Journal of Applied Physics, 2009, 105, 113502.	1.1	53
40	Cathodoluminescence study of dislocation-related luminescence from small-angle grain boundaries in multicrystalline silicon. Applied Physics Letters, 2009, 94, 112103.	1.5	17
41	Electron beam induced current investigation of stress-induced leakage and breakdown processes in high-k stacks. , 2009, , .		0
42	Electron-beam-induced current study of electrical activity of dislocations in 4H-SiC homoepitaxial film. Journal of Materials Science: Materials in Electronics, 2008, 19, 219-223.	1.1	14
43	Advanced semiconductor diagnosis by multidimensional electron-beam-induced current technique. Scanning, 2008, 30, 347-353.	0.7	4
44	Electron-beam-induced current study of stacking faults and partial dislocations in 4H-SiC Schottky diode. Applied Physics Letters, 2008, 93, .	1.5	39
45	Correlation between residual strain and electrically active grain boundaries in multicrystalline silicon. Applied Physics Letters, 2008, 93, .	1.5	34
46	Evaluation of minority-carrier diffusion length in n-type FeSi_2 single crystals by electron-beam-induced current. Applied Physics Letters, 2008, 92, 042117.	1.5	16
47	Lifetime and diffusion length of photogenerated minority carriers in single-crystalline n-type FeSi_2 bulk. Applied Physics Letters, 2008, 92, 192114.	1.5	17
48	Comparison of leakage behaviors in p- and n-type metal-oxide-semiconductor capacitors with hafnium silicon oxynitride gate dielectric by electron-beam-induced current. Applied Physics Letters, 2008, 92, 262103.	1.5	4
49	Enhanced red electroluminescence from a polycrystalline diamond film/Si heterojunction structure. Applied Physics Letters, 2007, 90, 161123.	1.5	9
50	Carrier Recombination Activity and Structural Properties of Small-Angle Grain Boundaries in Multicrystalline Silicon. Japanese Journal of Applied Physics, 2007, 46, 6489-6497.	0.8	103
51	Electron-beam-induced current study of grain boundaries in multicrystalline Si. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2908-2917.	0.8	20
52	Recombination behavior of nickel in cast multicrystalline silicon. Materials Science in Semiconductor Processing, 2006, 9, 304-307.	1.9	7
53	Electron-beam-induced current study of hydrogen passivation on grain boundaries in multicrystalline silicon: Influence of GB character and impurity contamination. Physica B: Condensed Matter, 2005, 364, 162-169.	1.3	39
54	Recombination activity of $\sim 3^\circ$ boundaries in boron-doped multicrystalline silicon: Influence of iron contamination. Journal of Applied Physics, 2005, 97, 033701.	1.1	84

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55	Copper precipitation in large-diameter Czochralski silicon. Journal of Applied Physics, 2005, 97, 094909.	1.1	19
56	Nickel precipitation in large-diameter Czochralski silicon. Physica B: Condensed Matter, 2004, 344, 407-412.	1.3	8
57	Influence of copper precipitation on oxygen precipitation in Czochralski silicon. Semiconductor Science and Technology, 2004, 19, 299-305.	1.0	15
58	Grain Boundaries in Multicrystalline Si. Solid State Phenomena, 0, 156-158, 19-26.	0.3	9
59	D-Line Emission from Small Angle Grain Boundaries in Multicrystalline Si. Solid State Phenomena, 0, 156-158, 561-565.	0.3	0
60	Analysis of Lattice Distortion in Multicrystalline Silicon for Photovoltaic Cells by Synchrotron White X-Ray Microbeam Diffraction. Materials Science Forum, 0, 725, 153-156.	0.3	1
61	Structural Study of Small Angle Grain Boundaries in Multicrystalline Si. Materials Science Forum, 0, 725, 157-160.	0.3	6
62	Statistical Consideration of Grain Growth Mechanism of Multicrystalline Si by One-Directional Solidification Technique. Solid State Phenomena, 0, 242, 35-40.	0.3	0
63	50 cm Size Seed Cast Si Ingot Growth and its Characterization. Solid State Phenomena, 0, 242, 30-34.	0.3	2
64	Effect of reactive gas condition on nonpolar AlN film growth on MnS/Si (100) by reactive DC sputtering. Japanese Journal of Applied Physics, 0, , .	0.8	1